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Phys. Rev. B 93, 121411 — Published 24 March 2016
DOI: 10.1103/PhysRevB.93.121411
Evidence for a new symmetry breaking mechanism reorienting quantum Hall nematics

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We report on the effect of in-plane magnetic field $B_\parallel$ on stripe phases in higher ($N = 2, 3$) Landau levels of a high-mobility 2D electron gas. In accord with previous studies, we find that a modest $B_\parallel$ applied parallel to the native stripes aligns them perpendicular to it. However, upon further increase of $B_\parallel$, stripes are reoriented back to their native direction. Remarkably, applying $B_\parallel$ perpendicular to the native stripes also aligns stripes parallel to it. Thus, regardless of the initial orientation of stripes with respect to $B_\parallel$, stripes are ultimately aligned parallel to $B_\parallel$. These findings provide evidence for a $B_\parallel$-induced symmetry breaking mechanism which challenges current understanding of the role of $B_\parallel$ and should be taken into account when determining the strength of the native symmetry breaking potential. Finally, our results might indicate nontrivial coupling between the native and external symmetry breaking fields, which has not yet been theoretically considered.

PACS numbers: 73.43.Qt, 73.63.Hs, 73.40.-c

Electronic liquid crystal-like phases, termed electron nematics or stripes, are expected to form in a wide variety of condensed matter systems [1–5]. A two-dimensional electron gas in GaAs/AlGaAs hosts the first, and perhaps the most striking, realization of such phases [6–11]. Stripes in a two-dimensional electron gas form due to interplay between exchange and direct Coulomb interactions [6, 7, 10, 11] and are manifested by the resistivity minima (maxima) in the easy (hard) transport direction near half-integer filling factors, $\nu = 9/2, 11/2, 13/2, ...$ when the system is cooled below $T \approx 0.1$ K. With very few exceptions [12–14], stripes in GaAs are aligned along (110) direction, but what exactly causes such orientation remains unknown [13, 15, 16].

While the origin of the native symmetry-breaking potential responsible for preferred stripes orientation remains elusive, its magnitude was routinely obtained from experiments employing in-plane magnetic field $B_\parallel$ which provides an external symmetry-breaking field competing with and overcoming the native one. Our current understanding of $B_\parallel$-induced symmetry-breaking potential is based on finite thickness effects [17, 18], which favor stripes perpendicular to $B_\parallel$, consistent with previous experiments [13, 19–23]. The same approach successfully explains $B_\parallel$-induced stripes in both single-subband [19, 20, 24–26] and double-subband [27] systems.

In this Rapid Communication we re-examine the effect of in-plane magnetic field on quantum Hall stripes in ultrahigh quality GaAs quantum wells. In agreement with early experiments [19–21], we find that a $B_\parallel \lesssim 0.4$ applied parallel to the native stripes aligns stripes perpendicular to it. Remarkably, upon further increase of $B_\parallel$, stripes are reoriented back to their native direction, i.e., parallel to $B_\parallel$. When $B_\parallel$ is applied perpendicular to the native stripes, we also find that stripes are oriented parallel to $B_\parallel$. We thus conclude that there exist a new $B_\parallel$-induced symmetry-breaking potential which challenges our understanding of the role of $B_\parallel$ and must be taken into account when determining the strength of the native symmetry-breaking potential. In contrast to the well-established $B_\parallel$-induced symmetry-breaking potential originating from finite thickness effects, new symmetry-breaking potential exhibits high sensitivity to spin and Landau level indices. Finally, our results suggest a nontrivial coupling between the native and external symmetry-breaking fields, which has not yet been theoretically considered and might provide an important clue to unveiling the origin of the native symmetry-breaking potential.

The sample used in our study is a $4 \times 4$ mm square cleaved from a symmetrically doped, $30$ nm-wide GaAs/AlGaAs quantum well. Electron density and mobility were $n_e \approx 2.9 \times 10^{11}$ cm$^{-2}$ and $\mu \approx 1.6 \times 10^7$ cm$^2$/Vs, respectively. Eight indium contacts were fabricated at the corners and mid-side of the sample. The longitudinal resistances, $R_{xx}$ and $R_{yy}$, were measured using four-terminal, low-frequency lock-in technique; the current (typically 10 nA) was sent through the mid-side contacts and the voltage drop was recorded between the corner contacts. An in-plane magnetic field was introduced by tilting the sample about $\hat{x}$ or $\hat{y}$ axis, in two separate cooldowns. The data were taken at $T \approx 20$ mK.

In Fig. 1(a) we present an example of stripes in perpendicular magnetic field near $\nu = 9/2$, characterized by $R_{xx} \gg R_{yy}$, indicating stripes oriented along $\hat{y} = (110)$ direction. When $B_\parallel$ is applied parallel to the native stripes ($B_\parallel = B_\parallel$), at $\theta_y = 12^\circ$ stripes reorient along $\hat{x}$-direction (perpendicular to $B_\parallel$), as anticipated [see Fig. 1(b)]. Surprisingly, upon further increase of $B_\parallel$, at $\theta_y = 46^\circ$ stripes are reoriented again, back to their na-
tive direction and are now aligned parallel to $B_\parallel$ [see Fig.1(c)]. When $B_\parallel$ is applied perpendicular to the native stripes ($B_\parallel = B_x$), at $\theta_x = 42^\circ$ stripes are reoriented along $\hat{z}$-direction, again aligning parallel to $B_\parallel$ [see Fig.1(d)]. We thus conclude that, regardless of the orientation of $B_\parallel$, ultimately, stripes align parallel to $B_\parallel$.

Figure 1(e) shows the resistance anisotropy $A_{R} \equiv (R_{xx} - R_{yy})/(R_{xx} + R_{yy})$ vs $B_\parallel$ (left panel) and $B_y$ (right panel). Starting from $A_R \approx 1$, with increasing $B_y$, $A_R$ vanishes at $B_y \approx 0.4$ T, reaches $A_R \approx -1$, turns around, disappears again at $B_y \approx 1.1$ T, and finally returns to $A_R \approx 1$. With increasing $B_x$, $A_R$ vanishes at $B_x \approx 0.4$ T and then approaches $A_R \approx -1$. Taken together, the data in Fig.1 clearly demonstrate the existence of a mechanism which favors stripes along $B_\parallel$. As we show next, this mechanism is relevant at other filling factors although it shows sensitivity to both the spin index $\sigma$ and the Landau level index $N$.

Figure 2 shows the phase diagram of stripe orientations at $\nu = 9/2, 11/2, 13/2$ and 15/2 for (a) $B_\parallel = B_y$ and (b) $B_\parallel = B_x$. The regions with vertical (horizontal) lines represent stripes along $\hat{y}$ ($\hat{x}$), demarcated by the characteristic fields $B_{1y}$ (open dots), $B_{2x}$ [panel (b)] and $B_{2y}$ [panel (a)] (solid dots). For comparison, $B_{2y}$ (crosses) are added to panel (b) at $\nu = 9/2$ and 13/2. Dashed lines represent $B_\parallel$ at marked tilt angles. $R_{xx}$ (solid line) and $R_{yy}$ (dotted line) vs $\nu$ at (c) $\theta_y = 46^\circ$ and (d) $\theta_y = 57^\circ$. 

**Fig. 1.** $R_{xx}$ (solid line) and $R_{yy}$ (dotted line) versus $\nu$ at (a) $\theta = 0^\circ$, (b) $B_\parallel = B_y$ and $\theta_y = 12^\circ$, (c) $B_\parallel = B_y$ and $\theta_y = 46^\circ$, and (d) $B_\parallel = B_x$ and $\theta_x = 42^\circ$. (e) Resistance anisotropy $A_R \equiv (R_{xx} - R_{yy})/(R_{xx} + R_{yy})$ as a function of $B_\parallel$ (left) and $B_\parallel = B_y$ (right) at $\nu = 9/2$. The inset shows the stripes orientation and the direction of $B_\parallel$. 

**Fig. 2.** Evolution of stripe orientation at $\nu = 9/2, 11/2, 13/2$ and 15/2 for (a) $B_\parallel = B_y$ and (b) $B_\parallel = B_x$. The regions with vertical (horizontal) lines represent stripes along $\hat{y}$ ($\hat{x}$), demarcated by the characteristic fields $B_{1y}$ (open dots), $B_{2x}$ [panel (b)] and $B_{2y}$ [panel (a)] (solid dots). For comparison, $B_{2y}$ (crosses) are added to panel (b) at $\nu = 9/2$ and 13/2. Dashed lines represent $B_\parallel$ at marked tilt angles. $R_{xx}$ (solid line) and $R_{yy}$ (dotted line) vs $\nu$ at (c) $\theta_y = 46^\circ$ and (d) $\theta_y = 57^\circ$. 
considerably smaller for $\sigma = +1/2$ than $\sigma = -1/2$.

The sensitivity of $B_{2x}$ and $B_{2y}$ to $\sigma$ and $N$ is also evident in the raw data presented in Fig. 2(c) and (d). For $B_{||} = B_y$ and $\theta_y = 46^\circ$ [see Fig. 2(c)], the stripes at $\nu = 9/2$ have reoriented back to their native direction (along $y$ axis) as manifested by $R_{xx} \gg R_{yy}$. The data at $\nu = 13/2$ suggest that the (second) reorientation is about to happen at this filling factor as well. However, stripes at $\nu = 11/2$ and 15/2 are still oriented along $\hat{x}$ direction, as $R_{xx} < R_{yy}$. For $B_{||} = B_x$ and $\theta_x = 57^\circ$ [see Fig. 2(d)], stripes both at $\nu = 9/2$ and 13/2 have reoriented along $\hat{x}$ axis, stripes at $\nu = 11/2$ are undergoing the reorientation, while stripes at $\nu = 15/2$ are still oriented along $\hat{y}$ direction.

To compare the magnitudes of $B_{2x}$ and $B_{2y}$ we add $B_{2y}$ (crosses) to Fig. 2(b) and observe that $B_{2y}$ is close to $B_{2x}$ at both $\nu = 9/2$ and 13/2. Combined with qualitatively identical dependence on $\sigma$ and $N$, this observation suggests that the reorientations characterized by $B_{2x}$ and $B_{2y}$ are of similar origin. We can now classify the reorientations into two types. The first type, which aligns stripes perpendicular to $B_{||}$, is characterized by $B_{1y}$ that is not sensitive to $\sigma$ and decreases with $N$. The second type aligns stripes parallel to $B_{||}$ and is characterized by $B_{2x}$ and $B_{2y}$ that depend on $\sigma$ and increase with $N$. The data at $\nu = 9/2$ also suggest that the mechanism responsible for reorientation of the first (second) type dominates at lower (higher) $B_{||}$.

The reorientation of the first type is well understood in terms of finite thickness effects [17, 18]. The $B_{||}$-induced anisotropy energy can be defined as $E_{1A} = E_{1||} - E_{1\perp}$, where $E_{1||}$ and $E_{1\perp}$ are optimized energies per electron of a stripe state parallel and perpendicular to $B_{||}$, respectively. For a single-subband system, $E_{1A} > 0$ and increases monotonically with $B_{||}$ [17, 21]. While $E_{1A}$ could change sign in systems with two occupied subbands, such systems do not exhibit native stripes at $B_{||} = 0$ and $E_{1A}$ is insensitive to $\sigma$ [17, 27]. We thus conclude that reorientations of the second type, favoring stripes parallel to $B_{||}$, have a distinct physical origin.

Furthermore, since $E_{1A}(B_x) = E_{1A}(B_y)$ for $B_x = B_y$ [17, 18], we can conclude that the mechanism responsible for reorientation of the second type lacks such symmetry. Indeed, if we assume that the anisotropy energy due to the second mechanism, $E_{2A}$, is the same for $B_{||}$ applied along $\hat{x}$ or $\hat{y}$ directions, one would expect, in the absence of native symmetry-breaking potential, $B_{2x} = B_{2y}$ at a given $\nu$; a native symmetry-breaking potential favoring stripes along $\hat{y}$ direction would then lead to $B_{2x} > B_{2y}$. In contrast, our data show exactly the opposite, and, e.g., at $\nu = 9/2$, $B_{2y} \approx 1.0$ T is considerably larger than $B_{2x} \approx 0.4$ T. We thus conclude that $E_{2A}$ must depend on the direction of $B_{||}$, suggesting possible coupling of $B_{||}$ to native symmetry-breaking potential [29]. A proposal considering a combination of Rashba and Dresselhaus spin-orbital interactions as the origin of the native symmetry-breaking potential [15, 30, 31] seems to indicate that the effects of $B_{||}$ on such native stripe states should be sensitive to its orientation with respect to the crystal axes. However, a study of the interplay between $B_{||}$ and spin-orbital interactions was left for future work.

Despite our lack of understanding of the mechanism responsible for the second type of reorientation, our experimental results unambiguously demonstrate that two competing mechanisms must be incorporated in any complete theory of reorientation of quantum Hall nematics. Another important implication of our findings is related to the identification of the native symmetry-breaking potential, whose strength was traditionally obtained by calculating $E_{1A}$ at $B_{||} = B_{1c}$. In light of clear evidence for the second mechanism and its possible coupling to the native symmetry-breaking potential and/or $E_{1A}$, this approach must be reexamined.

We thank G. Csathy, L. Engel, Y. Liu, B. Skinner, M. Shayegan, B. Shklovskii, and I. Sodemann for discussions. We thank G. Jones, S. Hamas, T. Murphy, J. Park, and A. Suslov for technical technical support. The work at Minnesota (Purdue) was supported by the U.S. Department of Energy, Office of Science, Basic Energy Sciences, under Award # ER 46640-SC0002567 (DE-SC0006671). Q.S. acknowledges The University of Minnesota Doctoral Dissertation Fellowship. Experiments were performed at the National High Magnetic Field Laboratory, which is supported by NSF Cooperative Agreement No. DMR-0654118, by the State of Florida, and by the DOE.

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[28] Qualitatively consistent with our observations, early experiments [19] have found that, when $B_0$ is applied perpendicular to stripes, the anisotropy is affected more at $\nu = 9/2$ and 13/2 than at $\nu = 11/2$ and 15/2.

[29] An alternative scenario is that, the effect of $B_0$ is modified by disorder which is anisotropic along the two crystal axes [22]. However, effect of disorder on stripes orientation has not been studied theoretically and it seems unlikely that such a mechanism would depend on $\sigma$.

[30] We note that the anisotropy energy due to this mechanism also shows oscillating behavior with $\sigma$.

[31] Recent experiments [13] have found that the quantum well symmetry has a minor role in deciding the stripes orientation, suggesting that spin-orbital interaction [15] is unlikely to be the major mechanism for the native symmetry breaking.